

Schottky Barrier Diode

FUJ2E

Features

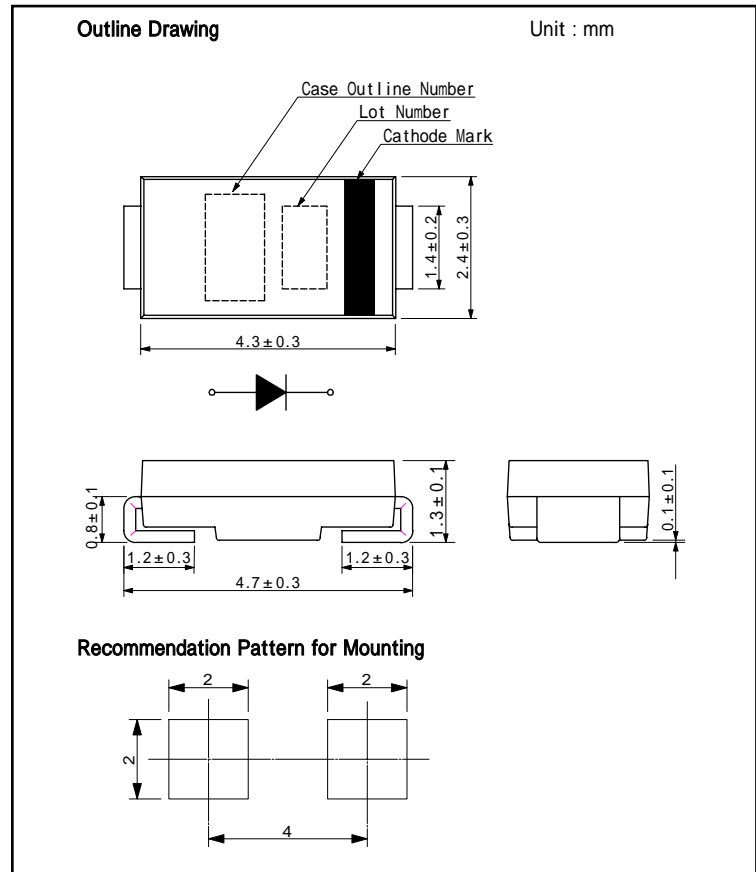
- Compact size, low-profile (h=1.3mm).
- Long battery lifetime realized by employing the schottky barrier diode with low loss characteristics.
- Various types are available including a large-current (3A) type.
- Inside-bent pin structure maintains high-reliability.

Applications

- Hybrid ICs.
- High-frequency rectification.
- Switching regulators.
- Preventing power supply from counter-flowing.
- Avoiding reverse current by wrong setting of a battery.

Structures

- Resin molded, Silicon Schottky Barrier diode.
- Marking symbol : [J2E]
- Weight : 0.04g
- Terminal plating : Sn
- Conforms to RoHS regulations



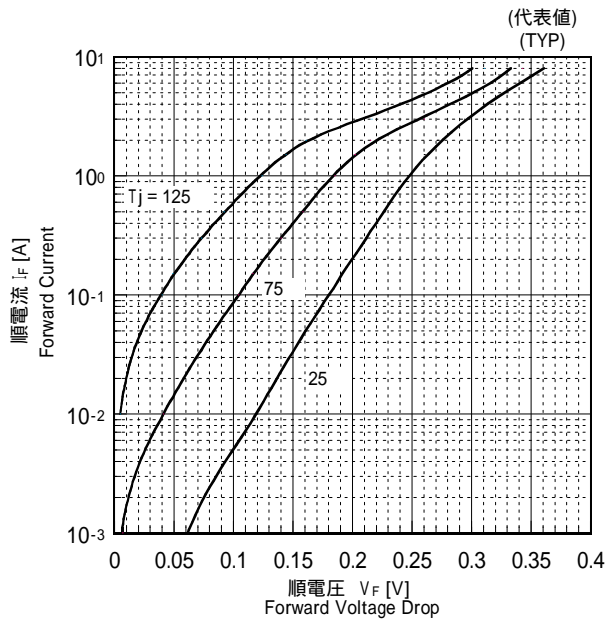
Absolute Maximum Ratings (Ta=25)

Items	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RM}		20	V
Non-Repetitive Peak Reverse Voltage	V_{RSM}		25	V
Average Forward Current	I_o	$T = 64$, Rectangular wave 180° , $V_R=5V$	3	A
Peak Forward Surge Current	I_{FSM}	$T_j=25$, 50Hz, Single-phase, Half sin wave , Non - Repetitive	30	A
Operating Junction Temperature	T_j		-40 ~ +125	
Storage Temperature	T_{stg}		-40 ~ +150	

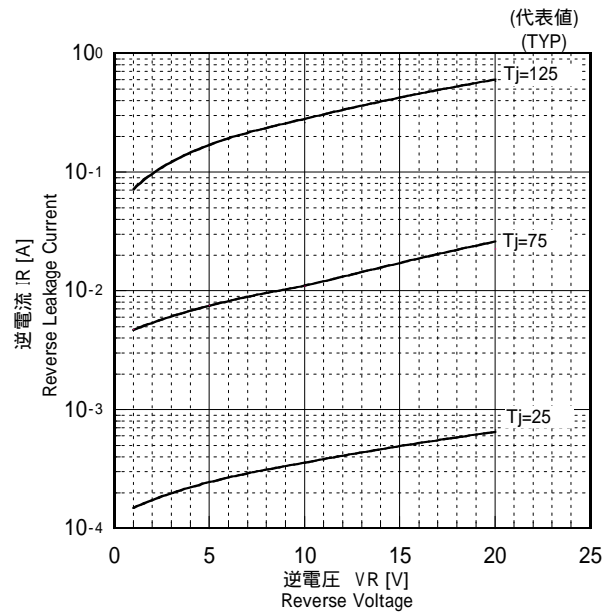
Electrical Characteristics (Tj=25)

Items	Symbol	Conditions	TYP.	MAX.	Unit
Forward Voltage Drop	V_{F1}	$I_F=1A$	0.25	-	V
	V_{F2}	$I_F=3A$	0.30	0.33	V
Reverse Current	I_R	$V_R=20V$	-	2.0	mA
Junction Capacitance	C_j	$V_R=10V$	180	-	pF
Terminal Resistance(junction to lead)	$R_{th(j-l)}$	Cathode Lead Temperature	-	35	/W

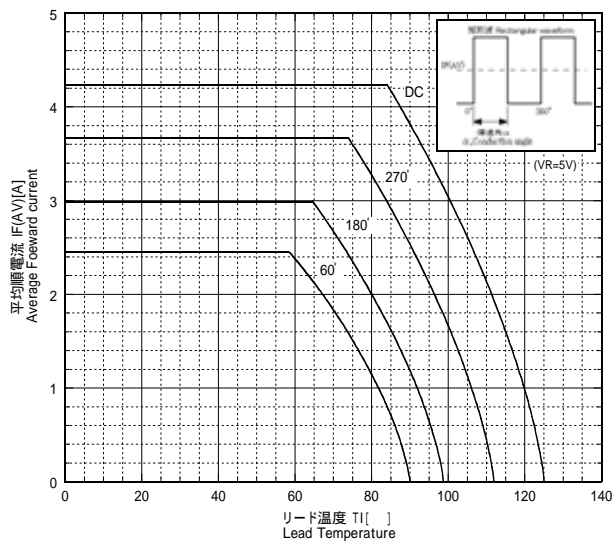
Characteristics Diagrams



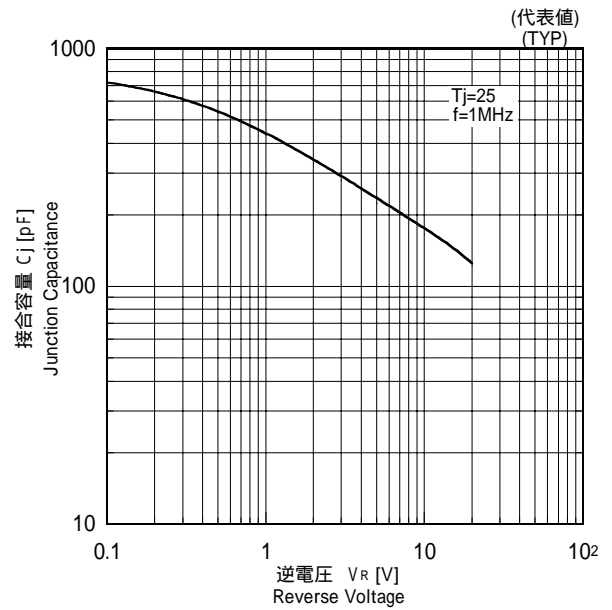
FORWARD CHARACTERISTICS



REVERSE CHARACTERISTICS



AVERAGE RECTIFIED FORWARD CURRENT



TYPICAL JUNCTION CAPACITANCE